Philips Components-Signetics

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Status	Product Specification
Memory Produ	ucts

DESCRIPTION

The 82S23 and 82S123 are field programmable, which means that custom patterns are immediately available by following the Signetics Generic I fusing procedure. The 82S23 and 82S123 devices are supplied with all outputs at logical Low. Outputs are programmed to a logic High level at any specified address by fusing a Ni-Cr link matrix.

These devices include on-chip decoding and 1 Chip Enable input for memory expansion. They feature either Open Collector or 3-State outputs for optimization of word expansion in bused organizations.

Ordering information can be found on the following page.

The 82S23 and 82S123 devices are also processed to military requirements for operation over the military temperature range. For specifications and ordering information, consult the Signetics Military Data Handbook.

FEATURES

82S23 82S123

Address access time: 50ns max

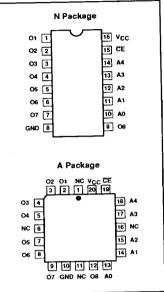
256-bit TTL bipolar PROM

- Power dissipation: 1.3mW/bit typ
- Input loading: -100µA max
- On-chip address decoding
- One Chip Enable input
- Output options:
 N82S23: Open Collector
 N82S123: 3-State
- No separate fusing pins
- Unprogrammed outputs are Low level
- Fully TTL compatible

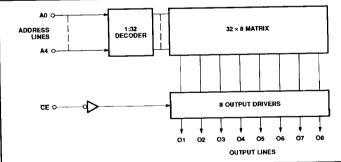
APPLICATIONS

- Prototyping/volume production
- Sequential controllers
- Format conversion
- Hardwired algorithms
- Random logic
- Code conversion

PIN CONFIGURATIONS







256-bit TTL bipolar PROM (32 × 8)

82S23 / 82S123

ORDERING INFORMATION

DESCRIPTION	ORDER CODE
16-Pin Plastic Dual-In-Line 300mil-wide	N82S23 N, N82S123 N
20-Pin Plastic Leaded Chip Carrier 350mil-square	N82S23 A, N82S123 A

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
Vcc	Supply voltage	+7.0	V _{DC}
ViN	Input voltage	+5.5	V _{DC}
VOH	Output voltage High (82S23)	+5.5	V _{DC}
Vo	Output voltage Off-State (82S123)	+5.5	V _{DC}
Tamb	Operating temperature range	0 to +75	°C
T _{stg}	Storage temperature range	-65 to +150	℃

DC ELECTRICAL CHARACTERISTICS

 $0^{\circ}C \leq T_{amb} \leq +75^{\circ}C, 4.75V \leq V_{CC} \leq 5.25V$

SYMBOL	PARAMETER	TEST CONDITIONS ^{1,2}	LIMITS			UNIT	
			MIN	TYP ³	MAX		
Input voltag	je						
VIL	Low	V _{CC} = 4.75V			0.8	v	
VIH	High	$V_{CC} = 5.25V$	2.0			v	
VIC	Clamp	i _{IN} = -12mA			-1.2	v	
Output volt	age						
		CE = Low					
VOL	Low	l _{OUT} = 16mA			0.45	v	
V _{OH}	High	l _{OUT} = -2.0mA	2.4			v	
Input curre	nt						
կլ	Low	V _{IN} = 0.45V			-100	μΑ	
Iн	High	$V_{IN} = 5.5V$			50	μΑ	
Output cur	rent						
OLK	Leakage (82S23)	CE = High, V _{OUT} = 5.5V			40	μA	
loz	Hi-Z state (82S123)	CE = High, V _{OUT} = 5.5V			40	μA	
		$\overline{CE} = High, V_{OUT} = 0.5V$			-40	μA	
los	Short circuit (82S123)4	\overline{CE} = Low, V_{OUT} = 0V, High stored	-15		-90	mA	
Supply cur	rent ⁵		• • • • • • • • • • • • • • • • • • • •				
lcc		V _{CC} = 5.25V			96	mA	
Capacitanc	æ						
		CE = High, V _{CC} = 5.0V					
CiN	Input	V _{IN} = 2.0V		5		ρF	
COUT	Output	V _{OUT} = 2.0V		8		pF	

NOTES:

1. Positive current is defined as into the terminal referenced.

2. All voltages with respect to network ground terminal. 3. Typical values are at $V_{CC} = 5V$, $T_{amb} = +25^{\circ}C$. 4. Duration of short circuit should not exceed 1 second. 5. Measured with all inputs grounded and all outputs open.

82S23 / 82S123

256-bit TTL bipolar PROM (32×8)

AC ELECTRICAL CHARACTERISTICS

 $B_1 = 270\Omega$, $B_2 = 600\Omega$, $C_1 = 30pF$, $0^{\circ}C < T_{amb} < +75^{\circ}C$, $4.75V \le V_{CC} \le 5.25V$

SYMBOL	PARAMETER	то	FROM	LIMITS			UNIT
				MIN	TYP ¹	MAX	
Access time ²							
t _{AA}		Output	Address		45	50	ns
t _{CE}		Output	Chip Enable			35	ns
Disable time ³							
tco		Output	Chip Disable			35	ns

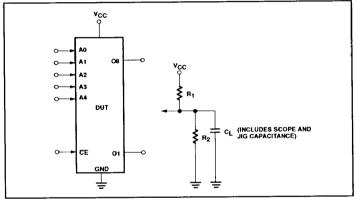
NOTES:

Typical values are $V_{CC} = 5V$, $T_{amb} = +25^{\circ}C$. Tested at an address cycle time of 1µs. 1.

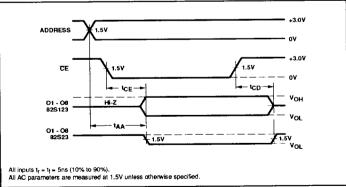
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3. Measured at a delta of 0.5V from Logic Level with $R_1 = 750\Omega$, $R_2 = 750\Omega$ and $C_L = 5pF$.

TEST LOAD CIRCUIT



VOLTAGE WAVEFORM



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